

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Please amend claim 12 as set forth below.

12. (Amended) A method, comprising:

etching a contact hole, through a first insulating layer comprising doped silicon dioxide, that is self-aligned with respect to a conductive structure that is formed over a substrate and includes [having] insulating sidewalls with an etch selectivity between the first insulating layer and the sidewall that is greater than ten to one, and an etch selectivity between the first insulating layer and the substrate that is greater than one hundred to one.

Please amend claim 14 as set forth below.

14. (Amended) The method of claim 12, further including:

forming [a] the first insulating layer comprising a high density plasma silicon dioxide having a concentration of phosphorous dopant that is greater than 5% by weight.

Please cancel claim 15.

Please amend claim 17 as set forth below.

17. (Amended) A method, comprising:

forming a hard mask comprising substantially undoped silicate glass over an insulating layer comprising doped silicon dioxide, the hard mask having openings over a contact hole location; and

forming a contact hole at the contact hole location through [an] the insulating layer between conducting structures separated from one another by less than 0.4 microns and having sidewalls, without forming a protective liner over the conducting structures[, wherein the insulating layer comprises silicon dioxide].